



NPN Silicon Power Transistor

Qualified per MIL-S-19500/207

Qualified Levels:
JAN

DESCRIPTION

This family of 2N1479 through 2N1482 medium-power, planar transistors are military qualified to the JAN level for high-reliability applications.

Important: For the latest information, visit our website <http://www.microsemi.com>.

FEATURES

- JEDEC registered 2N1479 through 2N1482 series
- JAN qualification are available per MIL-S-19500/207.
(See [part nomenclature](#) for all available options.)
- RoHS compliant versions available (commercial grade only)



TO-5 Package

APPLICATIONS / BENEFITS

- General purpose transistors for low power applications requiring high frequency switching
- Low package profile
- Military and other high-reliability applications

MAXIMUM RATINGS @ T_A = +25 °C unless otherwise noted

| Parameters / Test Conditions | Symbol | 2N1479 2N1481 | 2N1480 2N1482 | Unit |
|--|-----------------------------------|------------------|------------------|------|
| Collector-Emitter Voltage | V _{CEO} | 40 | 55 | V |
| Collector-Base Voltage | V _{CB0} | 60 | 100 | V |
| Emitter-Base Voltage | V _{EBO} | 12 | | V |
| Base Current | I _B | 1.0 | | A |
| Collector Current | I _C | 1.5 | | A |
| Operating & Storage Junction Temperature Range | T _J , T _{stg} | -65 to +200 | | °C |
| Thermal Resistance Junction-to-Case | R _{θJC} | 35 | | °C/W |
| Total Power Dissipation @ T _A = +25 °C ⁽¹⁾ | P _T | 1.0 | | W |

Notes: 1. For 1000 hours expected life at T_A = +25 °C

MSC – Lawrence

6 Lake Street,
Lawrence, MA 01841
Tel: 1-800-446-1158 or
(978) 620-2600
Fax: (978) 689-0803

MSC – Ireland

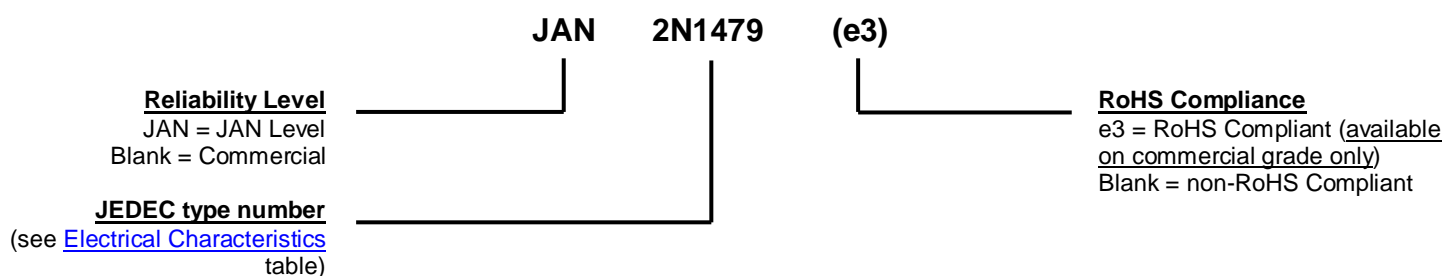
Gort Road Business Park,
Ennis, Co. Clare, Ireland
Tel: +353 (0) 65 6840044
Fax: +353 (0) 65 6822298

Website:

www.microsemi.com

MECHANICAL and PACKAGING

- CASE: Hermetically sealed steel base, nickel cap
- TERMINALS: Leads are gold plated kovar (Solder dip (Sn63/Pb37) is available upon special request. NOTE: Solder dipping will eliminate RoHS compliance.)
- MARKING: Part number, date code, manufacturer's ID
- POLARITY: NPN
- WEIGHT: Approximately 1.14 grams
- See [Package Dimensions](#) on last page.

PART NOMENCLATURE

SYMBOLS & DEFINITIONS

| Symbol | Definition |
|---------------|---|
| h_{FE} | Common-emitter static forward current transfer ratio: The ratio of the dc output current to the dc input current with the output voltage held constant. |
| I_B | Base current: The value of the dc current into the base terminal. |
| I_C | Collector current: The value of the dc current into the collector terminal. |
| I_E | Emitter current: The value of the dc current into the emitter terminal. |
| T_C | Case temperature: The temperature measured at a specified location on the case of a device. |
| $V_{(BR)CEO}$ | Collector-emitter breakdown voltage, base open. The breakdown voltage between the collector and emitter terminals when the collector terminal is biased in the reverse direction with respect to the emitter terminal, and the base terminal is open circuited. The collector terminal is considered to be biased in the reverse direction when it is made positive for npn transistors, or negative for pnp transistors, with respect to the emitter terminal. |
| V_{CB} | Collector-base voltage: The dc voltage between the collector and the base. |
| V_{CBO} | Collector-base voltage, emitter open: The voltage between the collector and base terminals when the emitter terminal is open-circuited. |
| V_{CC} | Collector-supply voltage: The supply voltage applied to a circuit connected to the collector. |
| V_{CE} | Collector-emitter voltage: The dc voltage between the collector and the emitter. |
| $V_{CE(sat)}$ | Collector-emitter saturation voltage: The voltage between the collector and emitter terminals under conditions of base current or base-emitter voltage beyond which the collector current remains essentially constant as the base current or voltage is increased. |
| V_{CEO} | Collector-emitter voltage, base open: The voltage between the collector and the emitter terminals when the base terminal is open-circuited. |
| V_{EB} | Emitter-base voltage: The dc voltage between the emitter and the base |
| V_{EBO} | Emitter-base voltage, collector open: The voltage between the emitter and base terminals with the collector terminal open-circuited. |

ELECTRICAL CHARACTERISTICS @ $T_A = +25\text{ }^\circ\text{C}$, unless otherwise noted
OFF CHARACTERISTICS

| Parameters / Test Conditions | Symbol | Min. | Max. | Unit |
|---|---------------|-----------|------|---------------|
| Collector-Emitter Breakdown Voltage $I_C = 50\text{ mA}$, 2N1479, 2N1481 2N1480, 2N1482 | $V_{(BR)CEO}$ | 40 55 | | V |
| Collector-Emitter Breakdown Voltage $V_{EB} = 1.5\text{ V}$, $I_C = 0.25\text{ mA}$ $V_{EB} = 1.5\text{ V}$, $I_C = 0.25\text{ mA}$ 2N1479, 2N1481 2N1480, 2N1482 | $V_{(BR)CEX}$ | 60 100 | | V |
| Collector-Base Cutoff Current $V_{CB} = 30\text{ V}$ $V_{CB} = 50\text{ V}$ 2N1479, 2N1481 2N1480, 2N1482 | I_{CBO1} | | 5.0 | μA |
| Emitter-Base Cutoff Current $V_{EB} = 12\text{ V}$ | I_{EBO} | | 10 | μA |

ON CHARACTERISTICS

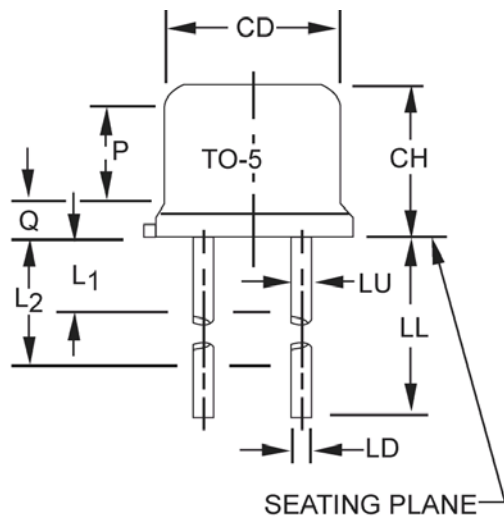
| Parameters / Test Conditions | Symbol | Min. | Max. | Unit |
|--|---------------|----------|--------------|------|
| Forward-Current Transfer Ratio $I_C = 200\text{ mA}$, $V_{CE} = 4.0\text{ V}$ 2N1479, 2N1480 2N1481, 2N1482 | h_{FE} | 20 35 | 60 100 | |
| Collector-Emitter Saturation Voltage $I_C = 200\text{ mA}$, $I_B = 20\text{ mA}$ $I_C = 200\text{ mA}$, $I_B = 10\text{ mA}$ 2N1479, 2N1480 2N1481, 2N1482 | $V_{CE(sat)}$ | | 0.75 0.75 | V |
| Base-Emitter Voltage Non-Saturation $I_C = 200\text{ mA}$, $V_{CE} = 4.0\text{ V}$ | V_{BE} | | 1.5 | V |

DYNAMIC CHARACTERISTICS

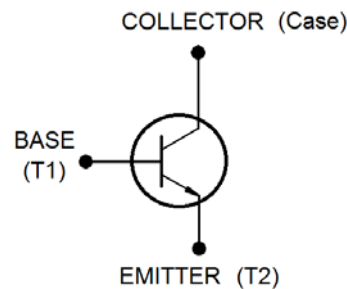
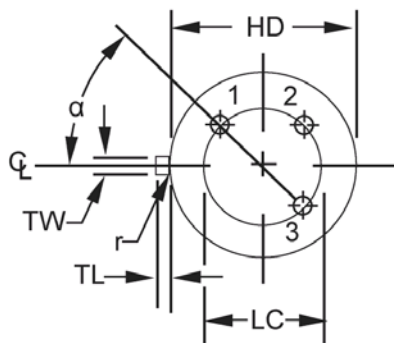
| Parameters / Test Conditions | Symbol | Min. | Max. | Unit |
|--|----------|------|------|------|
| Forward Current Cutoff Frequency $I_C = 5.0\text{ mA}$, $V_{CB} = 28\text{ V}$ | f_{ab} | 800 | | kHz |

SWITCHING CHARACTERISTICS

| Parameters / Test Conditions | Symbol | Min. | Max. | Unit |
|--|--------------------|------|------|---------------|
| Turn-On / Turn-Off Time $V_{CC} = 12\text{ V}$, $R_C = 59\ \Omega$, $I_{B0} = I_{B2} = 8.5\text{ mA}$; $I_{B1} = 20\text{ mA}$ | $t_{on} + t_{off}$ | | 25 | μs |

PACKAGE DIMENSIONS


| Symbol | Dimensions | | | | Note |
|----------|------------|-------|-------------|------|--------|
| | Inch | | Millimeters | | |
| | Min | Max | Min | Max | |
| CD | 0.305 | 0.335 | 7.75 | 8.51 | |
| CH | 0.240 | 0.260 | 6.10 | 6.60 | |
| HD | 0.335 | 0.370 | 8.51 | 9.40 | |
| LC | 0.200 TP | | 5.08 TP | | 10 |
| LD | 0.016 | 0.021 | 0.41 | 0.53 | 2, 9 |
| LL | 1.5 | 1.75 | 3.81 | 4.45 | 9 |
| LU | 0.016 | 0.019 | 0.41 | 0.48 | 3, 9 |
| L1 | - | 0.050 | - | 1.27 | 13 |
| L2 | 0.250 | - | 6.35 | - | 13 |
| P | 0.100 | - | 2.54 | - | 4 |
| Q | - | - | - | - | 5 |
| TL | 0.029 | 0.045 | 0.74 | 1.14 | 8 |
| TW | 0.028 | 0.034 | 0.71 | 0.86 | |
| r | - | 0.007 | - | 0.18 | Radius |
| α | 45° TP | | 45° TP | | 6 |


NOTES:

- Dimensions are in inches. Millimeters are given for information only.
- Measure in the zone beyond 0.250 (6.35 mm) from the seating plane.
- Measure in the zone 0.050 (1.27 mm) and 0.250 (6.35 mm) from the seating plane.
- Variations on Dim B in this zone shall not exceed 0.010 (0.25 mm).
- Outline in this zone is not controlled.
- When measured in a gauging plane 0.054 + 0.001 (1.37 mm + 0.03 mm) below the seating plane of the transistor max dia leads shall be within 0.007 (0.18mm) of their true location relative to a maximum width tab. Smaller dia leads shall fall within the outline of the max dia lead tolerance.
- Collector internally connected to case.
- Measured from the maximum diameter of the actual device.
- All 3 leads.
- Leads at gauge plane 0.054 inch (1.37 mm) +0.001 inch (0.03 mm) -0.000 inch (0.00 mm) below seating plane shall be within 0.007 inch (0.18 mm) radius of true position (TP) relative to tab. Device may be measured by direct methods or by gauge.



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- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

Телефон: 8 (812) 309 58 32 (многоканальный)

Факс: 8 (812) 320-02-42

Электронная почта: org@eplast1.ru

Адрес: 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.